

*CLAIM AMENDMENTS*

1. (Currently Amended) A semiconductor laser device comprising a dielectric multilayer film with a reflectance of at least 40% or more, formed on at least one of optical exit faces of a laser chip, wherein the dielectric multilayer film includes a ~~dielectric~~ film of tantalum oxide.

2. (Currently Amended) The semiconductor laser device according to Claim 1, wherein the dielectric multilayer film includes a ~~dielectric~~ film of aluminum oxide and the ~~dielectric~~ film of tantalum oxide.

3. (Currently Amended) The semiconductor laser device according to Claim 1, wherein the dielectric multilayer film includes a ~~dielectric~~ film of aluminum oxide ~~for a film~~ in contact with the laser chip, and ~~further includes a dielectric film of silicon oxide and the dielectric film of tantalum oxide.~~

4. (Currently Amended) The semiconductor laser device according to Claim 2, wherein the dielectric multilayer film is configured of a total of nine layers of, in sequence from the side in contact with the laser chip, an aluminum oxide film, a tantalum oxide film, and an aluminum oxide film.

5. (Currently Amended) The semiconductor laser device according to Claim 4, wherein each ~~thickness~~ of the first to eighth layers, from the side in contact with the laser chip, ~~in the dielectric multilayer film is~~ has a thickness equivalent to  $\lambda/4$  in terms of optical length ~~using, at an oscillation wavelength  $\lambda$  of the laser chip, and thickness of the ninth layer is~~ has a thickness equivalent to  $\lambda/2$  in terms of optical length.

6. (Currently Amended) The semiconductor laser device according to Claim 3, wherein the dielectric multilayer film is configured of a total of eight layers of, in sequence from the side in contact with the laser chip, an aluminum oxide film, a silicon film, a tantalum oxide film, a silicon film, a tantalum oxide film, a silicon film, a tantalum oxide film, and a silicon film.

7. (Currently Amended) The semiconductor laser device according to Claim 6, wherein ~~thickness of~~ the first layer, from the side in contact with the laser chip, ~~in the dielectric multilayer film is has a thickness~~ equivalent to  $\lambda/2$  in terms of optical length ~~using at an oscillation wavelength  $\lambda$  of the laser chip, and each thickness of the second to seventh layers is has a thickness~~ equivalent to  $\lambda/4$  in terms of optical length, and ~~thickness of the eighth layer is has a thickness~~ equivalent to  $\lambda/2$  in terms of optical length.